WHAT IS CLAIMED IS:

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1. A system for performing a scan of a portion of a specimen surface, comprising:

- a low coherence light energy generating device;
- a collimator for collimating light energy received from said low coherence light energy generating device;
- a diffraction grating for receiving light energy transmitted from said collimator and passing nonzero order light energy toward said specimen;
- a reflective surface for receiving predetermined order light energy from said diffraction grating;
- a second diffraction grating for receiving light reflected from said specimen and from said reflective surface;
 - a collimator for receiving light energy from said second diffraction grating; and
- a camera for receiving light energy from the 20 receiving collimator;

wherein said first diffraction grating passes light energy only over a portion of the specimen surface having predetermined standardized characteristics, said portion comprising less than half of the specimen surface.

- 2. The system of claim 1, wherein said predetermined order light energy is first order light energy.
- 3. The system of claim 2, wherein said reflective surface receives nonzero order light energy passed from said diffraction grating.

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- 4. The system of claim 2, further comprising a blocking element for blocking passage of zero order light energy received from said diffraction grating.
- 5. The system of claim 1, wherein the camera converts an elliptical image of said portion of said specimen into an image having an aspect ratio closer to 1:1.
 - 6. The system of claim 1, wherein each receiving collimator comprises at least one lens.

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- 7. The system of claim 2, wherein nonzero order light energy passes from said diffraction grating toward said reflective surface and said specimen.
- 8. The system of claim 2, wherein said first diffraction grating is optimized for zero intensity of its zero order.
- 9. The system of claim 2, further comprising means for rotating said specimen surface to expose alternate portions of said surface to said light energy.
- 20 10. The system of claim 1, wherein said first diffraction grating passes light energy over a portion of the specimen surface extending at least from a center of the specimen surface to an edge of the specimen surface.
- 25 11. The system of claim 1, wherein said system performs the scan of the portion of the specimen surface to assess at least one from a group comprising global planarization, erosion, and dishing.
- 12. The system of claim 1, wherein said specimen 30 comprises a CMP processed wafer, and said specimen comprises one from the group including:
 - (a) unpatterned wafers with film; 20253422v2

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- (b) patterned test wafer with test mask;
- (c) patterned production wafer with combination of product and test mask; and
- (d) patterned production wafers free of test 5 masks.
 - 13. The system of claim 1, wherein said system is integrated into a CMP processed wafer production line.
- 14. The system of claim 1, wherein the camera 10 has zoom capabilities.
 - 15. The system of claim 14, further comprising at least one translation means from the following:
 - (a) wafer translation means;
 - (b) interferometer translation means; and
 - (c) imaging system translation means;

wherein the translation means reduce the field of view generated by the zoom capabilities of the camera.

16. A method for inspecting a portion of a surface of a specimen, comprising the steps of:

transmitting light energy toward said specimen;
diffracting said light energy into predetermined
order light energy;

directing said diffracted light energy toward a predetermined portion of said specimen surface portion of said surface having predetermined standardized characteristics and simultaneously toward a reflective surface mounted substantially parallel to said specimen surface, wherein said predetermined portion comprises less than half of the specimen surface;

receiving predetermined order light energy reflected from said specimen and said reflective surface and combining the received light energy; and 20253422v2



directing said light energy to a light receiving device.

- 17. The method of claim 16, wherein predetermined order light energy comprises nonzero order light energy.
- 16. The method of claim 17, wherein diffracting step comprises diffracting for intensity of the zero order of the light energy received.
- 10 1\hat{\hat{N}}. The method of claim 16, further comprising the step of initially calibrating the system prior to said transmitting step.
 - W 18. The method of claim 16, wherein said light energy forms an image, and said directing step comprises altering the image aspect ratio.
 - 1) 19. The method of claim 16, wherein said method provides light energy to a strip extending from at least a center of said specimen to an edge of said specimen.
- 20. The method of claim 16, wherein said method 20 addresses and assesses at least one of the anomalies from a group comprising global planarization, erosion, and dishing.
- The method of claim 16, wherein said method is integrated into a CMP process line. 25
 - √[\] 22. The method of claim 16, wherein said specimen comprises a CMP processed wafer, and said specimen comprises one from the group including:
 - (a) unpatterned waters with film;
 - (b) patterned test wafer with test mask;
 - patterned production wafer with combination (c) of product and test mask; and

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- (d) patterned production wafers free of test masks.
- 23. The method of claim 16, wherein said light receiving device comprises a camera having zoom capabilities.
- 24. The method of claim 24, further comprising translating components to provide a reduced field of view when using the camera zoom capabilities.
- 25. A method for inspecting a surface of a specimen, said surface having a surface area, comprising:

disposing a swath of nonzero order light energy having approximate predetermined dimension across said said specimen while surface of simultaneously transmitting predetermined order light energy toward a reflective surface, said swath covering less than approximately half of the surface of area the specimen; and

combining light energy received from said surface and said reflective surface;

wherein said disposing step comprises disposing light energy to a portion of said surface having predetermined standardized characteristics.

- 26. The method of claim 23, wherein said 25 predetermined order light energy comprises nonzero order light energy.
 - 27. The method of claim 23, further comprising collimating light energy prior to said disposing step.
- 28. The method of claim 24, further comprising 30 diffracting light energy transmitted from said collimating step and passing diffracted nonzero order light energy toward said specimen.

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- 29. The method of claim 26, further comprising diffracting and collimating light received from said combining step.
- 30. The method of claim 27, further comprising blocking passage of zero order light energy received from said diffracting step.
 - 31. The method of claim 23, further comprising converting an image of said portion of said specimen into an image having an aspect ratio closer to 1:1.
 - 32. The method of claim 24, wherein said collimating step employs at least one lens.
 - 33. The method of claim 24, wherein said diffracting step is optimized for zero intensity of the zero order of the light energy.
- 15 34. The method of claim 23, wherein said method provides light energy to a strip extending from at least a center of said specimen to an edge of said specimen.
 - 35. The method of claim 23, wherein said method addresses and assesses at least one of the anomalies from a group comprising global planarization, erosion, and dishing.
 - 36. The method of claim 23, wherein said method is integrated into a CMP process line.
- 25 37. The method of claim 23, wherein said specimen comprises a CMP processed wafer, and said specimen comprises one from the group including:
 - (a) unpatterned wafers with film;
 - (b) patterned test wafer with test mask;
- 30 (c) patterned production wafer with combination of product and test mask; and





(d) patterned production wafers free of test masks.